JJMICROELECTRONICS

110V, 126A, 3.3mΩ N-channel Power SGT MOSFET

JMSH1102YC

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔVds TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

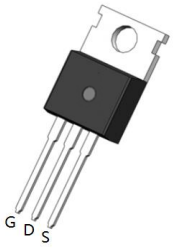
- Load Switch
- PWM Application
- Power Management

Product Summary

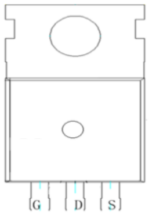
Parameters	Value	Unit
V_{DSS}	110	V
$V_{GS(th)\_Typ}$	3.1	V
I_D(@V_{GS}=10V)	126	A
$R_{DS(ON)\_Max}$(@V_{GS}=10V	3.3	mΩ

RoHS

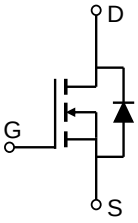
Lead-free Green



TO-220-3L Top View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Tube(pcs)	Per Carton (pcs)
JMSH1102YC	SH1102Y	NA	Tube	TO-220-3L	50	5000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		110	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	126	A
		T_C = 100°C	89	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		942	mJ
P_D	Power Dissipation	T_C = 25°C	137.0	W
		T_C = 100°C	54.8	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	44	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	110	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 88V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.1	3.1	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	3.3	4.2	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	2.1	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 55V, f = 1MHz	-	6718	-	pF
C_{oss}	Output Capacitance		-	947	-	pF
C_{rss}	Reverse Transfer Capacitance		-	28	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 55V, I_D = 20A	-	101	-	nC
Q_{gs}	Gate Source Charge		-	34	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	24	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 55V, I_D= 20A, R_{GEN} = 6.2Ω	-	32	-	ns
t_r	Turn-On Rise Time		-	46	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	79	-	ns
t_f	Turn-Off Fall Time		-	48	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	126	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	504	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	85	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	240	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=55V, V_G=10V, R_G=25ohm, L=3mH, I_{AS}=25.6A, V_{DD}=0V during time in avalanche.

3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

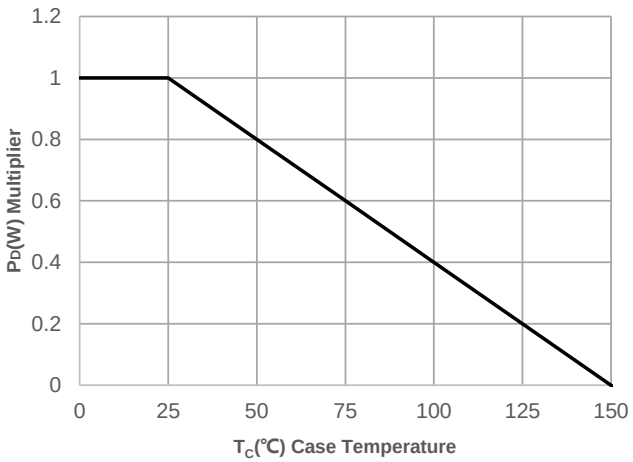


Figure 2: Current De-rating

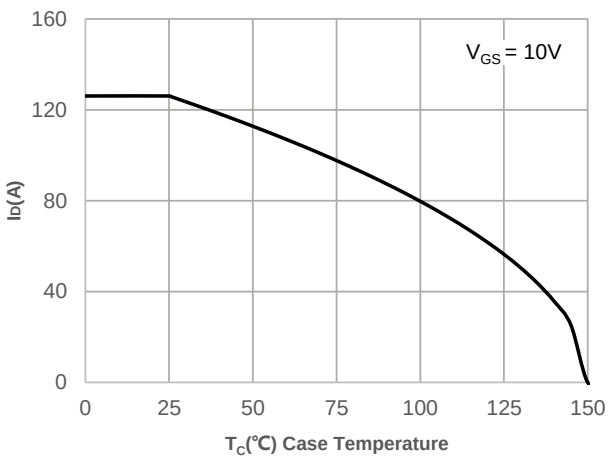


Figure 3: Normalized Maximum Transient Thermal Impedance

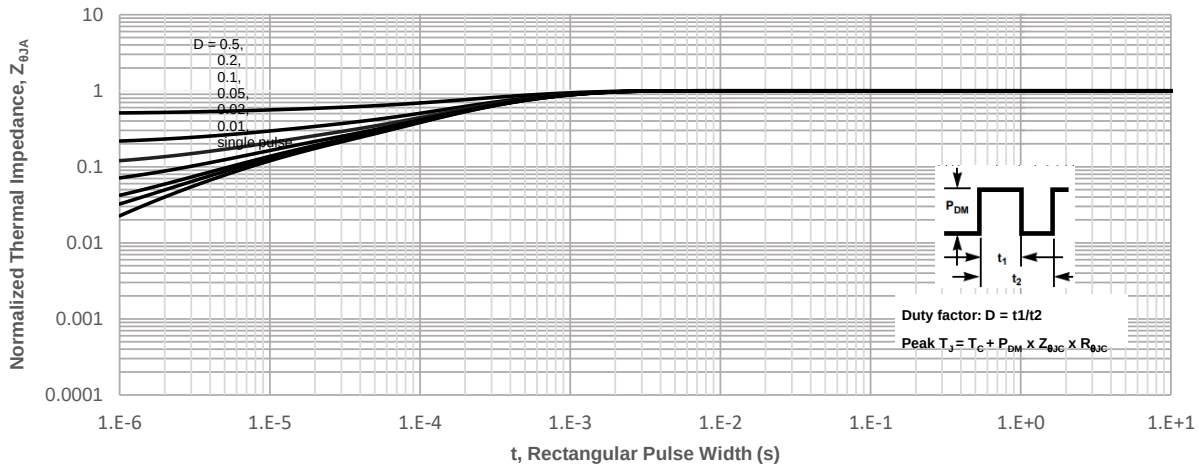
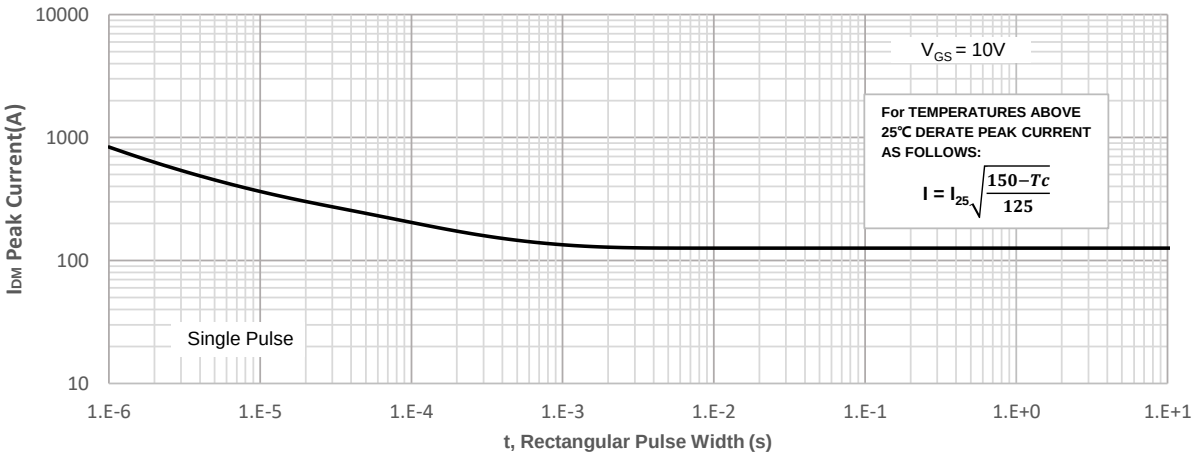


Figure 4: Peak Current Capacity



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Typical Performance Characteristics

Figure 5: Output Characteristics

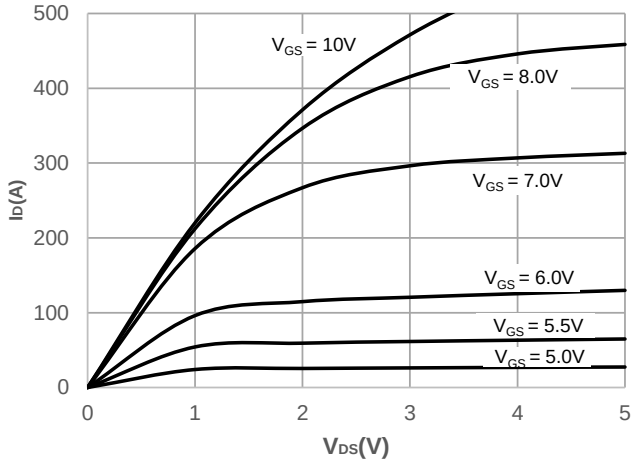


Figure 6: Typical Transfer Characteristics

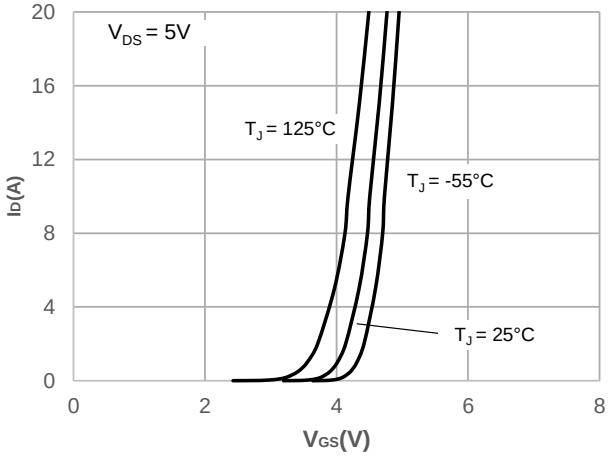


Figure 7: On-resistance vs. Drain Current

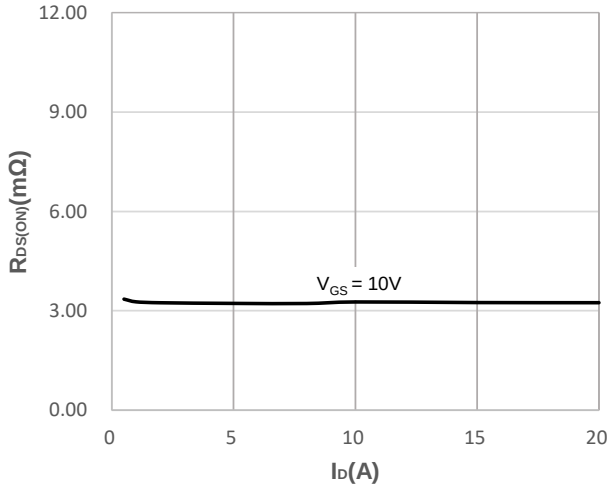


Figure 8: Body Diode Characteristics

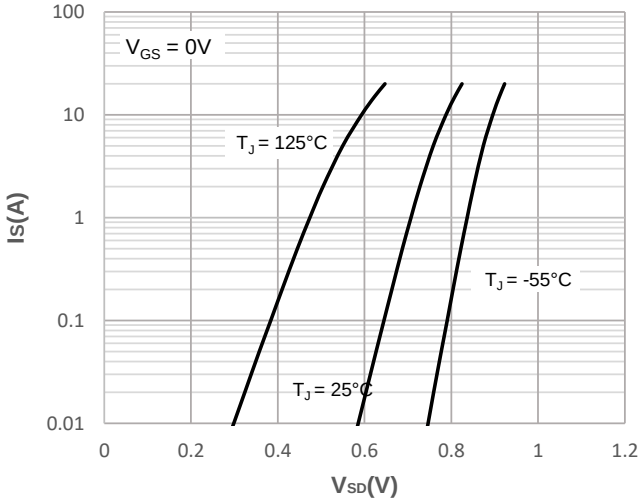


Figure 9: Gate Charge Characteristics

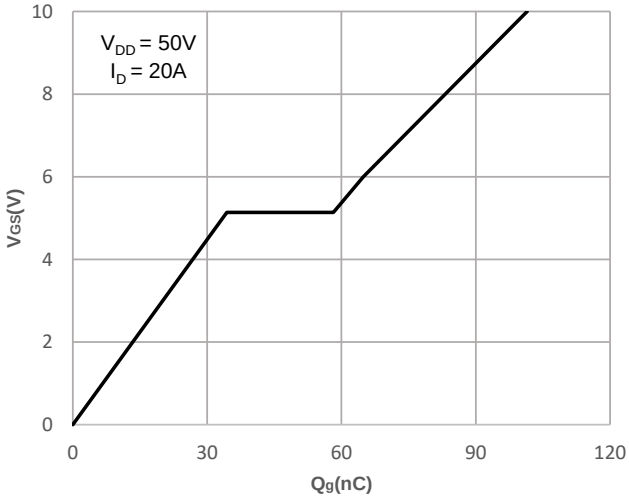
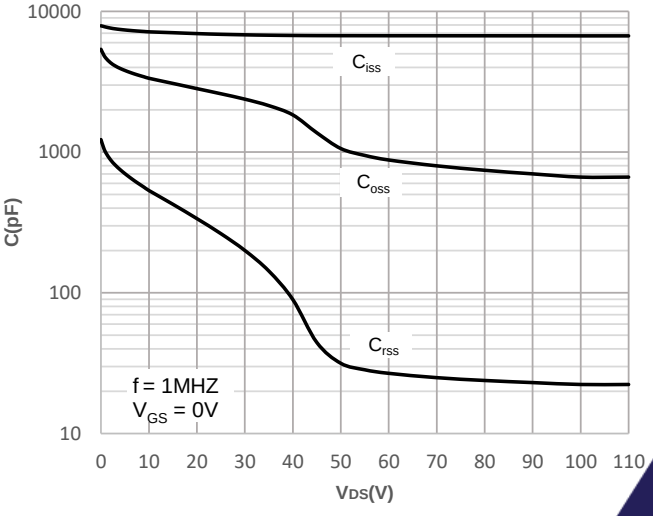


Figure 10: Capacitance Characteristics



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Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

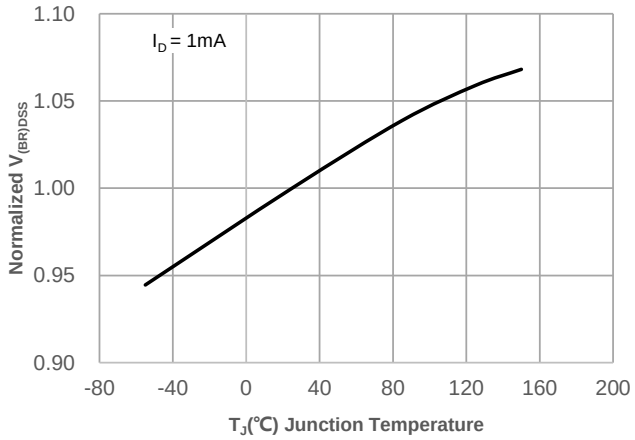


Figure 12: Normalized on Resistance vs. Junction Temperature

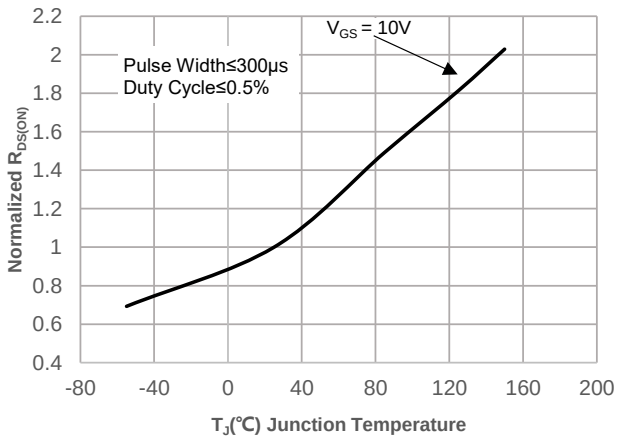


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

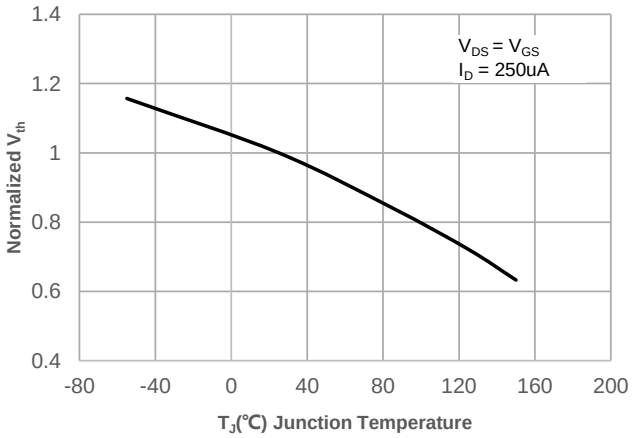


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

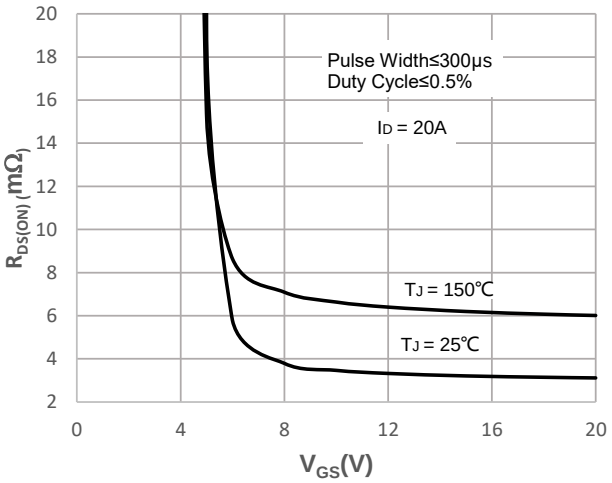
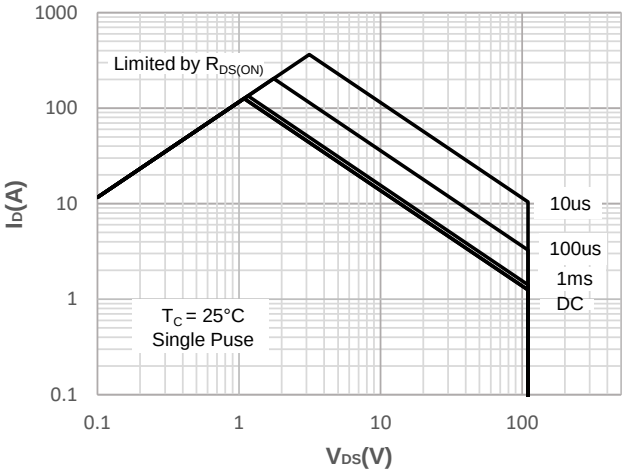


Figure 15: Maximum Safe Operating Area



Test Circuit

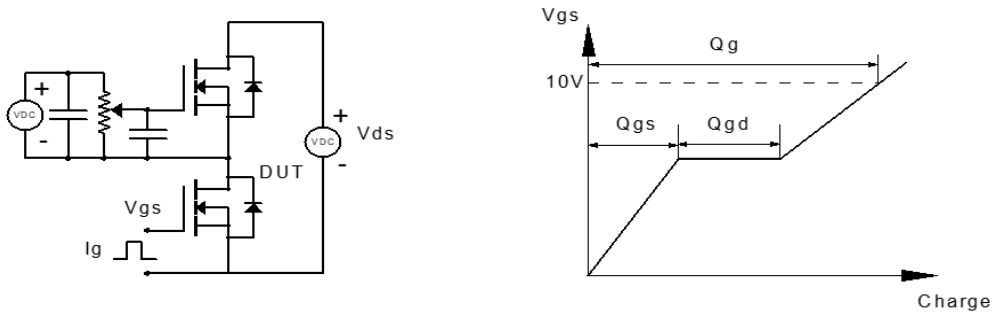


Figure 1: Gate Charge Test Circuit & Waveform

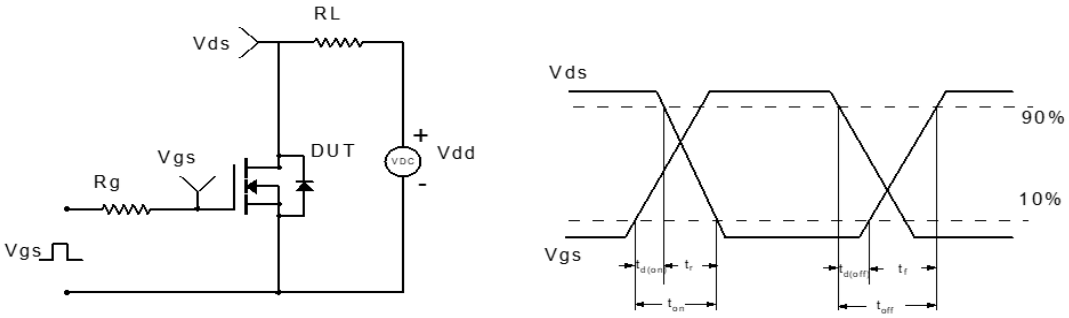


Figure 2: Resistive Switching Test Circuit & Waveform

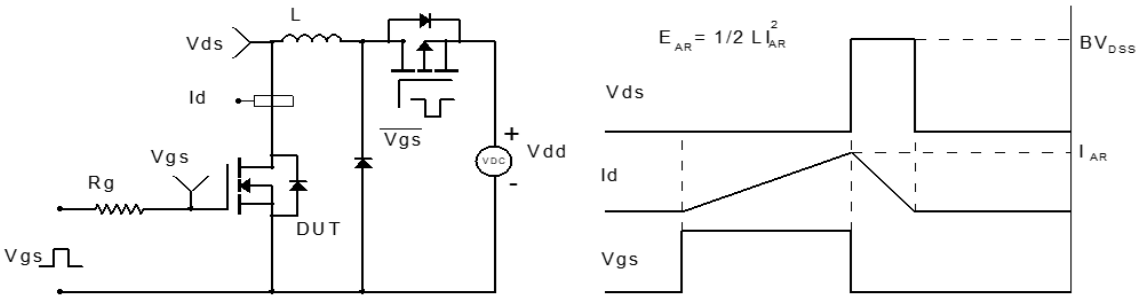


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

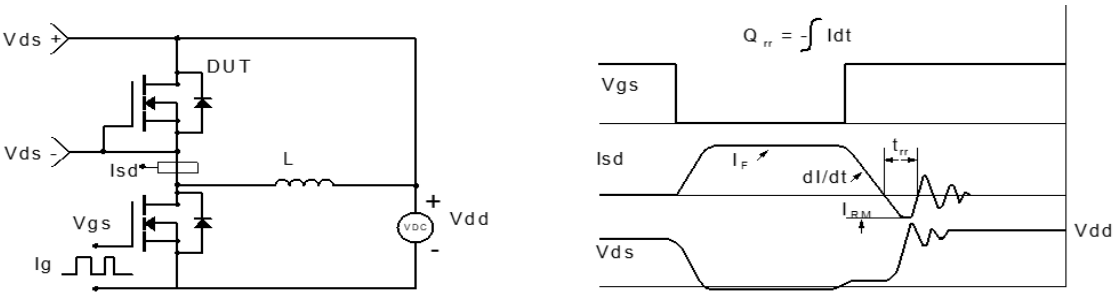


Figure 4: Diode Recovery Test Circuit & Waveform

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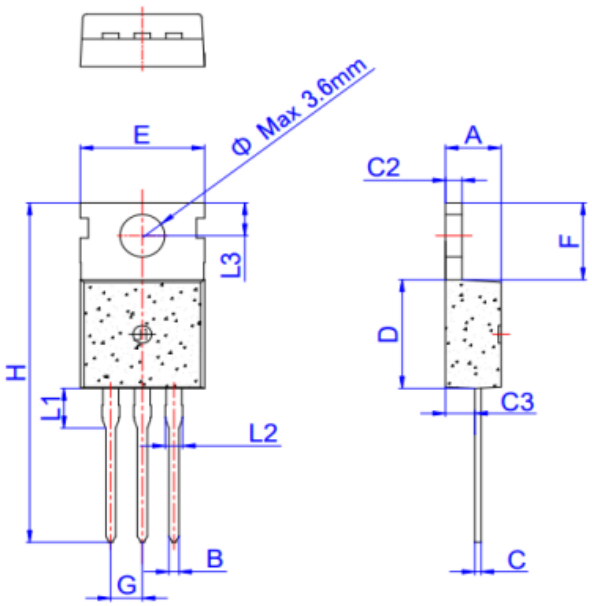
Package Mechanical Data(TO-220-3L)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	